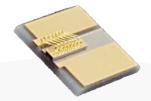
# High Power Laser Diode Chip on Carrier



### Part Number: COC-106

High Power Chip on Carriers Multi-Mode Fabry-Perot Pulsed Wavelength at 1550nm



#### **Features**

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard Chip on Carrier
- Cost Effective

### **Application**

- Laser Rangefinders
- Target Illumination



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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## Specification

#### COC-106



Optical	Symbol	Тур.	Units
Center Wavelength	λ <sub>c</sub>	1550	nm (±20)
Output Power (<10ns)*	Pout	40	watts (±10%)
Output Power (150ns)*	P <sub>out</sub>	24	watts (±10%)
Emitter Width	W	180	μm
Spectral Width FWHM	Δλ	15	nm
Slope Efficiency	η	0.25	W/A
Fast Axis Div.	Θ⊥	28	deg FWHM
Slow Axis Div.	Θ	14	deg FWHM
Electrical	Symbol		Units
Power Conversion Eff.	η	4	%
Operating Current (<10ns)	lop	160	Α
Operating Current (<150ns)	lop	80	А
Threshold Current	Ітн	2	Α
Operating Voltage	Vop	7	V
Duty Cycle	DC	0.1	%
Mechanical		Range	Units
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

\*Specified values are rated at a constant heat sink temperature of 20°C.

\*\*High temperature operation will reduce performance and MTTF.

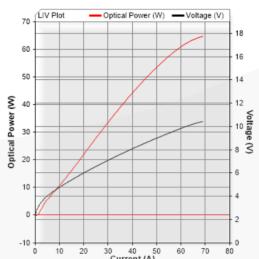
Unless otherwise indicated all values are nominal.

# High Power Laser Diode Chip on Carrier

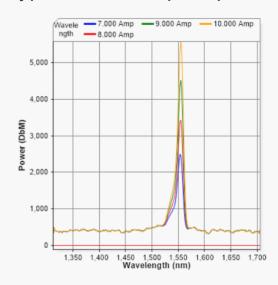


# SemiNex Laser Diodes COC-106 Graphs & Data

### Typical COC L-I-V Characteristics



#### Typical COC Output Spectrum



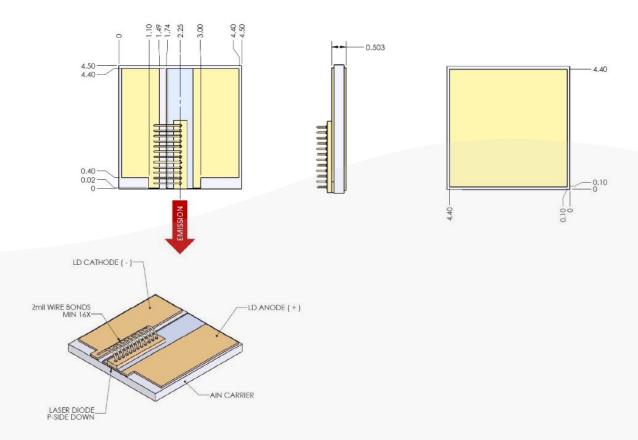
\*Tested with 150nsec pulse @ 0.1% Duty Cycle

# High Power Laser Diode Chip on Carrier



#### **Mechanical Drawing**





All statements, technical information and recommendations related to the product herein are based upon information believed to be reliable or accurate. The accuracy or completeness herein is not guaranteed, and no responsibility is assumed for any inaccuracies. The user assumes all risks and liability whatsoever in connection with the use of a product or its application. SemiNex Corporation reserves the right to change at any time without notice the design, specification, deduction, fit or form of its described herein, including withdrawal at any time of a product offered for sale herein. Users are encouraged to visit www.seminex.com for the latest data. SemiNex Corporation makes no representations that the products herein are free from any intellectual property claims of others. Please contact SemiNex for more information. 2024 SemiNex Corporation

